

• General Description

The AGM40P150C combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

• Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDS(ON)	ID
-40V	3.0mΩ	-148A

TO-220 Pin Configuration

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM40P150C	AGM40P150C	TO-220	---	---	1000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-40	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	-148	A
	Drain Current-Continuous(Tc=100°C)	-104	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	-592	A
PD	Maximum Power Dissipation(Tc=25°C)	132	w
	Maximum Power Dissipation(Tc=100°C)	53	w
EAS	Avalanche energy (Note 3)	847	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	62	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	0.95	°C/W

Table 2. P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

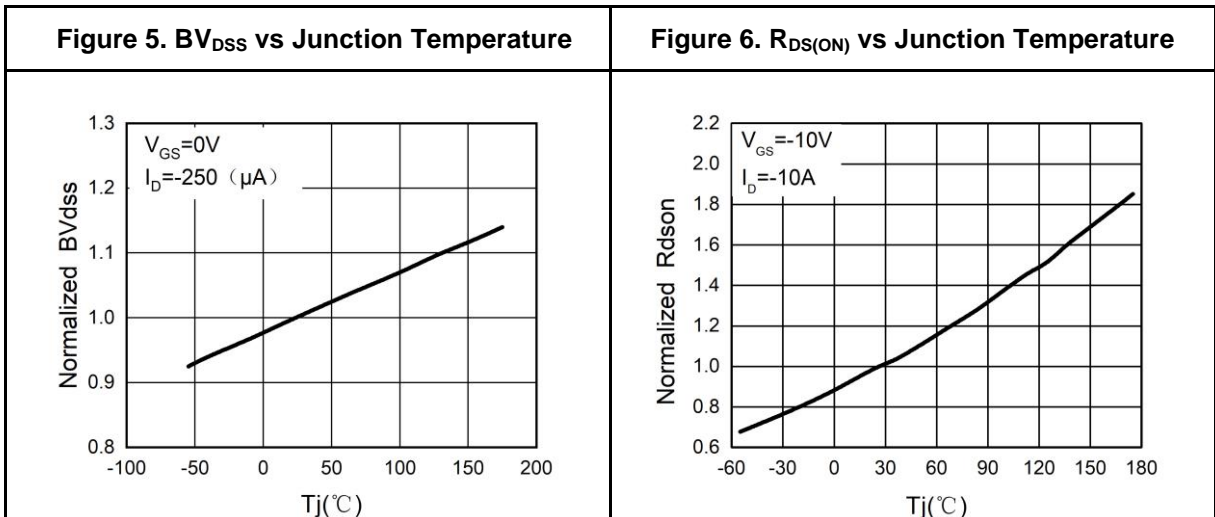
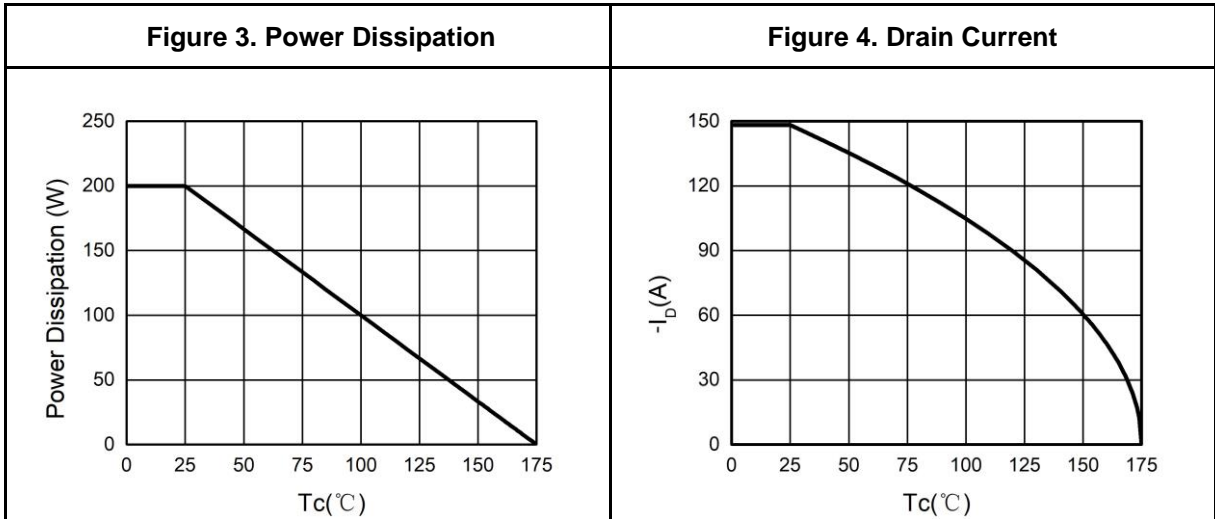
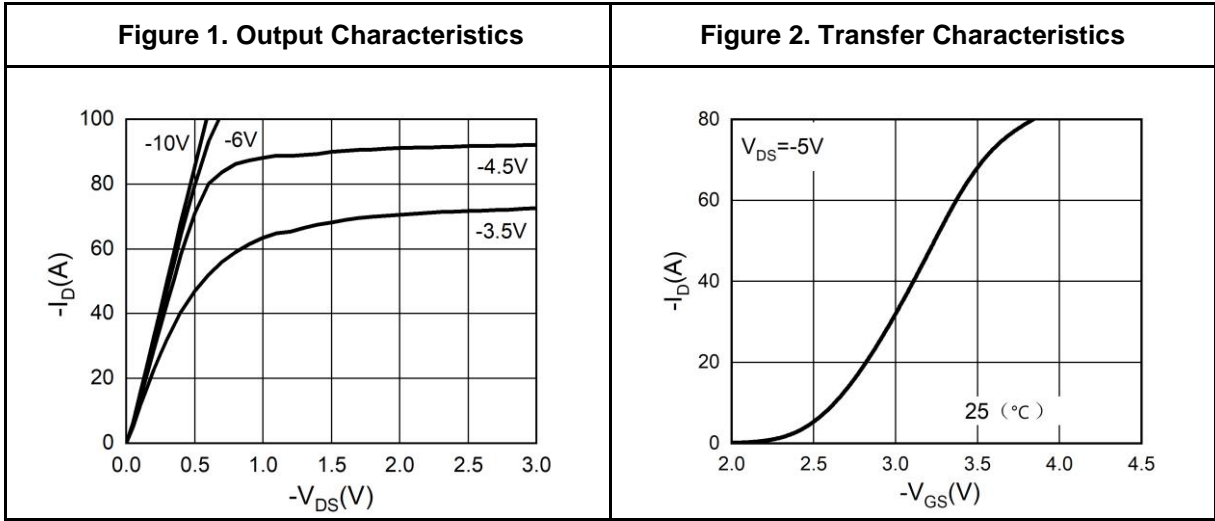
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-40	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-40V, VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±40V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=-250μA	-1.2	--	-2.2	V
gFS	Forward Transconductance	VDS=-5V, ID=-15A	--	60	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-20A	--	3.0	3.8	mΩ
		VGS=-4.5V, ID=-15A	--	4.0	5.6	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-20V, VGS=0V, F=1MHZ	--	10733	--	pF
Coss	Output Capacitance		--	770	--	pF
Crss	Reverse Transfer Capacitance		--	697	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	--	1.7	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V, VDS=-20V, RL=1Ω, RGEN=3.0Ω	--	19.6	--	nS
tr	Turn-on Rise Time		--	3.6	--	nS
td(off)	Turn-Off Delay Time		--	22.8	--	nS
tf	Turn-Off Fall Time		--	38	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-20V, ID=-20A	--	195	--	nC
Qgs	Gate-Source Charge		--	24.1	--	nC
Qgd	Gate-Drain Charge		--	39.9	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-148	A
VSD	Forward on Voltage	VGS=0V, IS=-20A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-20A , di/dt=100A/μs , TJ=25°C	--	51.1	--	ns
Qrr	Reverse Recovery Charge		--	125.2	--	nc

Notes 1.The maximum current rating is package limited.

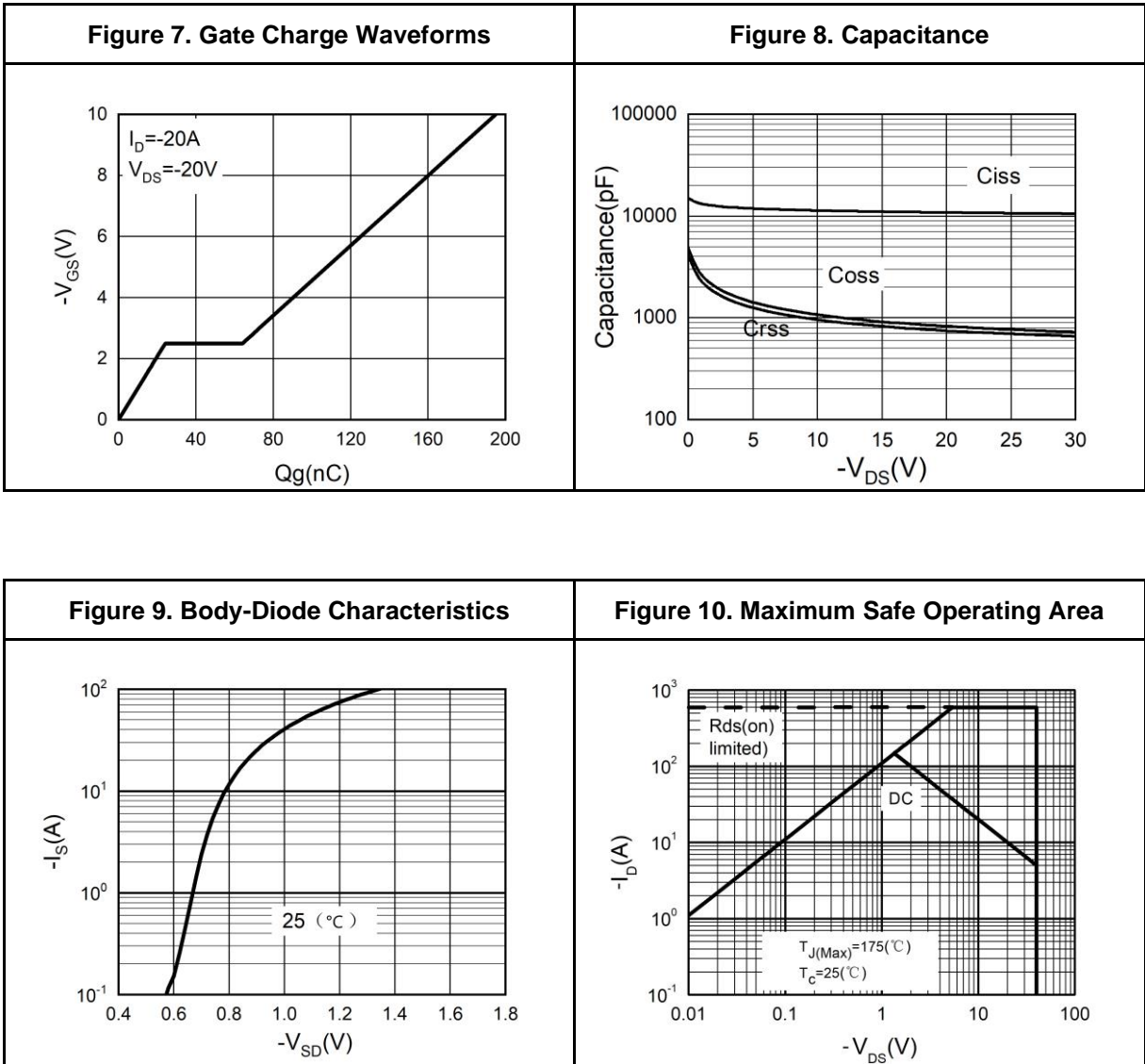
Notes2.Repetitive Rating: Pulse width limited by maximum junction temperature Notes

3.EAS condition: T_J=25°C, VDD=-30V, Vgs=-10V, ID=92A, L=0.2mH, RG=25ohm

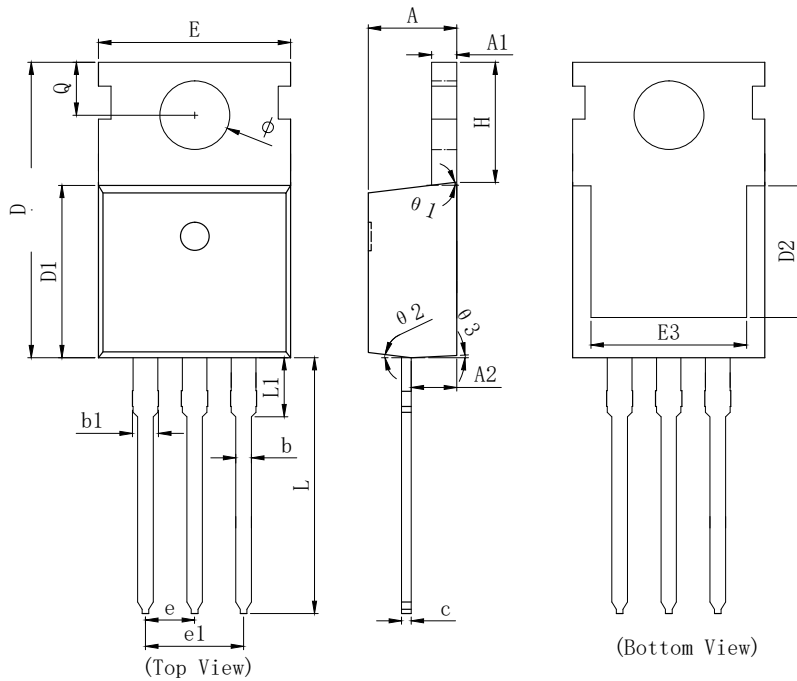
Typical Electrical And Thermal Characteristics (Curves)



Typical Electrical And Thermal Characteristics (Curves)



TO-220 PACKAGE INFORMATION



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	4.370	4.570	4.700
A1	1.250	1.300	1.400
A2	2.150	2.350	2.550
b	0.700	0.800	0.950
b1	1.170	1.270	1.470
c	0.450	0.500	0.600
D	15.100	15.600	16.100
D1	8.800	9.100	9.400
D2	5.500	6.300 REF	
E	9.700	10.000	10.300
E3	7.000	7.600 REF	
e	2.540 BSC		
e1	5.080 BSC		
L	13.200	13.500	13.800
L1		3.100	3.400
H	6.250	6.500	6.750
Φ	3.400	3.600	3.800
Q	2.600	2.800	3.000
θ 1	7° TYP		
θ 2	7° TYP		
θ 3	3° TYP		


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